









CEZ3P08A

-30V ▲ 7mΩ ▲ -62A ▲ Si MOSFET

SILICON Si MOSFET ▲ SMD type
P-channel enhancement mode
UL94V-0 rated flame retardant epoxy
PPAK5x6 package ▲ MSL 3
Super high dense cell density for extremely low R_{DS(ON)}
High power and current handling capability

MAXIMUM RATINGS

Parameter (T_c = 25°C, unless otherwise noted)		Characteristics
Drain-Source Voltage	V _{DS}	-30V
Gate-Source Voltage	V _{GS}	±20V
Continuous Drain Current at R _{TH_JC}	I _D	-62A
Continuous Drain Current at R _{TH_JA}	I _D	-21A
Pulsed Drain Current at R _{TH_JC} Note 1	I _{DM}	-248A
Pulsed Drain Current at R _{TH_JA} Note 1	I _{DM}	-84A
Maximum Power Dissipation	P _D	52W
Operating and Storage Temperature Range	T _J , T _{STG}	-55°C to +150°C

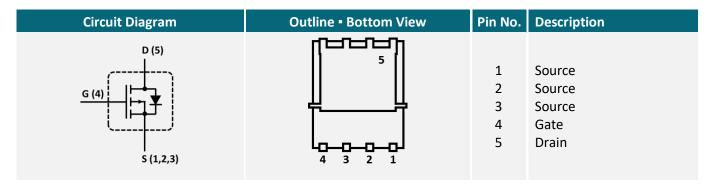
THERMAL CHARACTERISTICS

Parameter	Symbol	Limit
Thermal Resistance, Junction-to-Case	R _{TH_JC}	2.4°C/W
Thermal Resistance, Junction-to-Ambient Note 2	R _{TH_JA}	20°C/W

APPLICATIONS

DC/DC	DC	Load	Power	USB
Converter	Fan	Switches	Banks	Storage
=/			4	Ŷ

PIN DESCRIPTION





ELECTRICAL CHARACTERISTICS ▲ T_C = 25°C, unless otherwise noted

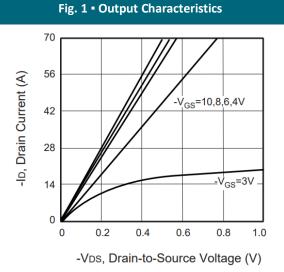
Item	Condition	Symbol	Min.	Тур.	Max.	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	$V_{GS} = 0V$, $I_D = -250\mu A$	BV _{DSS}	-30			V
Zero Gate Voltage Drain Current	V_{DS} = -30V, V_{GS} = 0V	I _{DSS}			-1	μΑ
Gate Body Leakage Current, Forward	$V_{GS} = 20V, V_{DS} = 0V$	I_{GSSF}			100	nA
Gate Body Leakage Current, Reverse	$V_{GS} = -20V, V_{DS} = 0V$	I_{GSSR}			-100	nA
On Characteristics Note 3						
Gate Threshold Voltage	$V_{GS} = V_{DS}, I_{D} = -250 \mu A$	$V_{GS(th)}$	-1		-3	V
Static Drain-Source On-Resistance	$V_{GS} = -10V, I_D = -10A$	R _{DS(ON)}		7	8.4	mΩ
Static Drain-Source On-Resistance	$V_{GS} = -4.5V$, $I_D = -10A$	R _{DS(ON)}		10.4	13.5	mΩ
Dynamic Characteristics Note 4						
Input Capacitance	$V_{DS} = -15V$, $V_{GS} = 0V$, $f = 1MHz$	C _{ISS}		2020		pF
Output Capacitance	$V_{DS} = -15V$, $V_{GS} = 0V$, $f = 1MHz$	Coss		390		pF
Reverse Transfer Capacitance	V_{DS} = -15V, V_{GS} = 0V, f = 1MHz	C _{RSS}		170		pF
Switching Characteristics Note 4						
Turn-On Delay Time	V_{DD} = -15V, V_{GS} = -10V, I_D = -10A, $R_{G(ext)}$ = 6Ω	t _{D(ON)}		18		ns
Turn-On Rise Time	V_{DD} = -15V, V_{GS} = -10V, I_{D} = -10A, $R_{G(ext)}$ = 6Ω	t _R		8		ns
Turn-Off Delay Time	V_{DD} = -15V, V_{GS} = -10V, I_{D} = -10A, $R_{G(ext)}$ = 6Ω	$t_{D(OFF)}$		108		ns
Turn-Off Fall Time	V_{DD} = -15V, V_{GS} = -10V, I_{D} = -10A, $R_{G(ext)}$ = 6Ω	t _F		31		ns
Total Gate Charge	V_{DD} = -15V, V_{GS} = -5V, I_D = -10A	Q_{G}		24		nC
Gate Source Charge	$V_{DD} = -15V$, $V_{GS} = -5V$, $I_{D} = -10A$	Q_{GS}		7		nC
Gate Drain Charge	$V_{DD} = -15V$, $V_{GS} = -5V$, $I_{D} = -10A$	Q_{GD}		10		nC
Drain-Source Diode Characteristics a	nd Maximum Ratings					
Drain-Source Diode Forward Current Note3		I _S			-47	Α
Drain-Source Diode Forward Voltage Note3	$V_{GS} = 0V$, $I_S = -13A$	V_{SD}			-1.1	V

Notes

- 1: Repetitive Rating: Pulse width limited by maximum junction temperature
- 2: Surface Mounted on FR4 Board, t ≤ 10 sec
- 3: Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 4: Guaranteed by design, not subject to production testing.



REFERENCE DATA A TYPICAL DEVICE PERFORMANCE



100 (V) 80 60 100 60 T_J=125°C 0 1 2 3 4 5 6

-Vgs, Gate-to-Source Voltage (V)

Fig. 2 • Transfer Characteristics

3000 C_{iss}

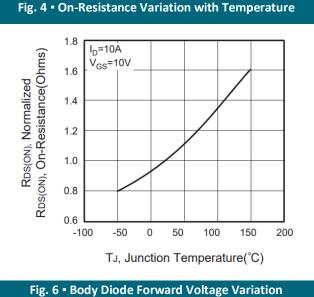
2500 C_{iss}

2000 C_{iss}

1500 C_{rss}

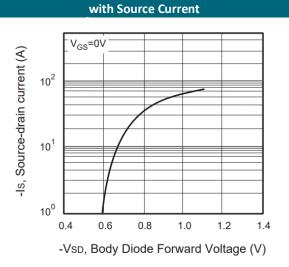
-Vps, Drain-to-Source Voltage (V)

Fig. 3 • Capacitance



V_{DS}=V_{GS} Gate-Source Threshold Voltage I_D=250μΑ Vтн, Normalized 1.1 1.0 0.9 8.0 0.7 0.6 -50 -25 0 25 50 75 100 125 150 TJ, Junction Temperature(°C)

Fig. 5 • Gate Threshold Variation with Temperature





REFERENCE DATA A TYPICAL DEVICE PERFORMANCE

Fig. 7 • Gate Charge

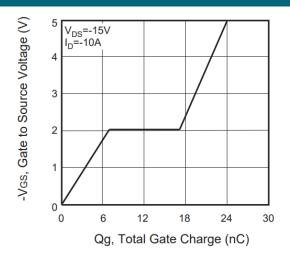


Fig. 8 • Maximum Safe Operating Area

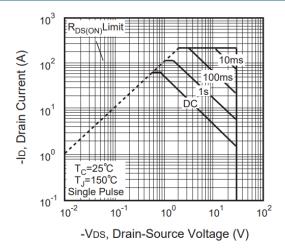


Fig. 9 • Breakdown Voltage Variation vs. Temperature

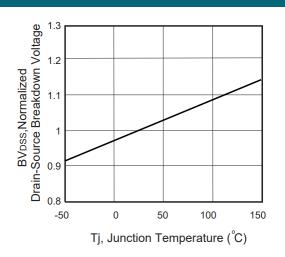


Fig. 10 • Switching Test Circuit

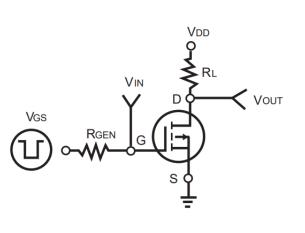
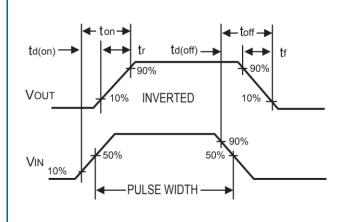


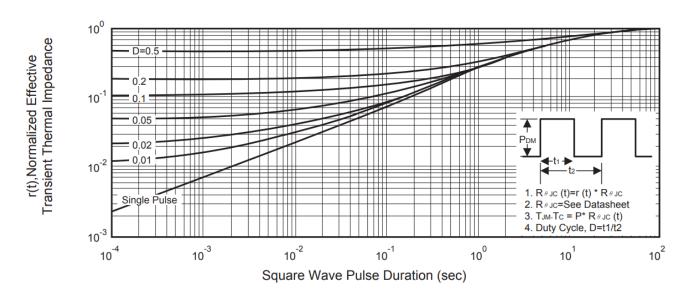
Fig. 11 • Switching Waveforms



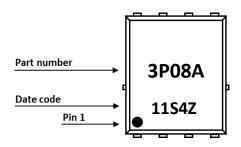


REFERENCE DATA A TYPICAL DEVICE PERFORMANCE

Fig. 12 • Normalized Thermal Transient Impedance Curve

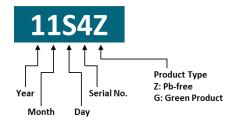


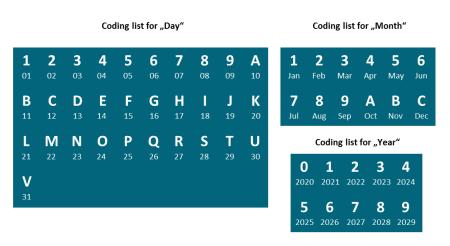
PART MARKING



DATE CODE

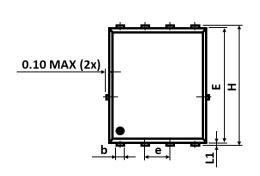
Example: 11S4Z

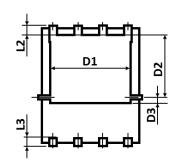


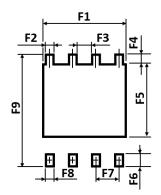


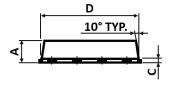


PACKAGE OUTLINE AND RECOMMENDED PAD LAYOUT









Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
Α	0.800	-	1.170
b	0.340	-	0.490
С	0.200	-	0.340
D	4.800	-	5.100
D1	3.800	-	4.200
D2	3.180	-	3.780
D3	0.150	-	0.360

Sym	Millimeters (Min.)		
E	5.650	-	5.900
e		1.270 TYP	
Н	5.900	-	6.150
L1	0.050	-	0.250
L2	0.380	-	0.620
L3	0.380	-	0.750

Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
F1	-	4.500	-
F2	-	0.500	-
F3	-	0.770	-
F4	-	0.550	-
F5	-	3.650	-

Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
F6	-	0.800	-
F7	-	1.270	-
F8	-	0.500	-
F9	-	6.250	-

Notes: 1. The suggested land pattern dimensions have been provided for reference only.

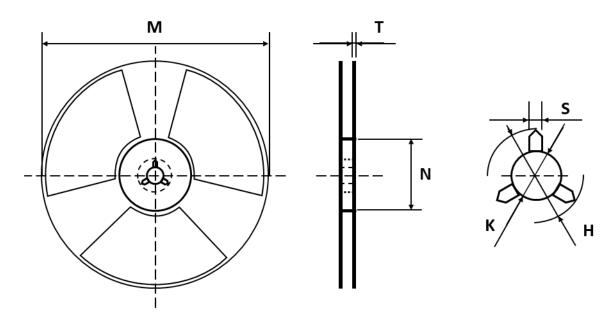
2. For further information, please reference document IPC-7351A.

ORDERING INFORMATION

Part Number	Package	Packing	Reel Qty.	Inner Box Qty.	Outer Box Qty.
CEZ3P08A	PPAK 5x6	Reel	2,500pcs	5,000pcs	40,000pcs

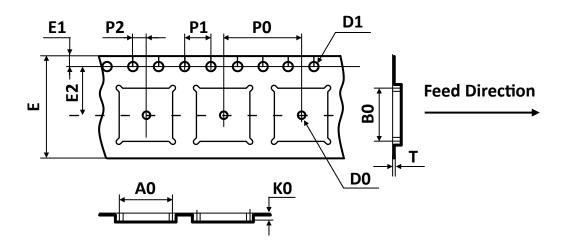


REEL DIMENSIONS ▲ All dimensions in mm



Tape Size	Reel Size	M	N	T	н	К	S
		Ø330.00	Ø100.00	2.10	22.00	13.00	2.00
12mm	Ø330	±2.00	±1.00	±0.20	±0.50	+0.50	±0.50
		±2.00	±1.00	10.20	10.30	-0.20	±0.50

TAPE DIMENSIONS ▲ All dimensions in mm

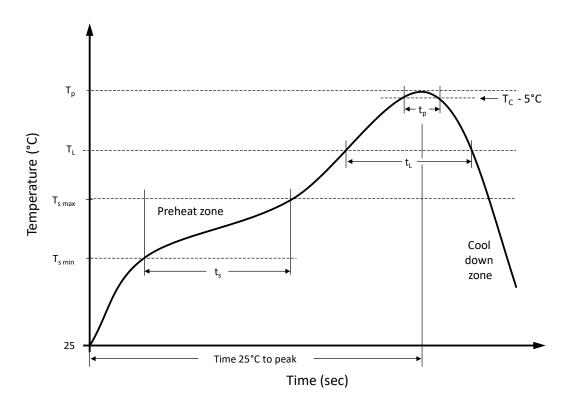


Package	Α0	В0	КО	D0	D1	Е	E1	E2	P0	P1	P2	T
	6.50	5.28	2.00	1.50	1.50	12.00	1.75	5.50	8.00	4.00	2.00	0.25
PPAK 5x6	±0.10	±0.10	±0.10	±0.25	±0.10	+0.30	±0.10	±0.05	±0.10	±0.10	±0.05	±0.02

Note: All dimensions meet EIA-481-D requirements.



RECOMMENDED REFLOW SOLDERING PROFILE



Recommended reflow soldering conditions ▲ **Refer to JEDEC J-STD-020E**

Profile Features		Sn-Pb Eutetic Assembly	Pb-Free Assembly
Preheat temperature min.	$T_{s min}$	100 °C	150 °C
Preheat temperature max.	T _{s max}	150 °C	200 °C
Preheat time t _s from T _{s min} to T _{s max}	ts	120 seconds	120 seconds
Ramp-up rate (T₁ to Tp)		max. 3 °C/second	max. 3 °C/second
Liquidous temperature	T_L	183 °C	217 °C
Time t _L maintained above T _L	t _L	150 seconds max.	150 seconds max.
Peak package body temperature	Tp	235°C	260°C
Timeframe of within 5°C below and up to max actual peak body temperature	t _p	20 seconds max.	30 seconds max.
Ramp-down rate (T _L to T _p)		max. 6 °C/second	max. 6 °C/second
Time 25°C to peak temperature		max. 6 minutes	max. 8 minutes



REVISION TABLE

Revision	Date	Status	Notes
001	30/09/2022	Initial release	Initial publication

DISCLAIMER

Except for the written expressed warranties, MGT does not implicitly, by assumption or whatever else, warrant, under-take, promise any other warranty or guaranty for any MGT product.

All information and technical specifications made available by MGT are for guidance only and we reserve the right to change or modify them without prior notice. Unless expressly stated in writing by MGT, we reject any guarantees, obligations, or warranties.

All MGT products with the technical specifications described are suitable for use in certain applications. Operating, production, storage and environmental conditions can have a massive influence on the parameters mentioned in the data sheets, which cause the performance to vary over time.

It is subject to the user's duty of care to design and validate his products in such a way that appropriate measures are taken, such as protective circuits or redundant systems to ensure the safety standards required in the application.

MGT components are not designed or rated for use in life support, rescue, safety critical, military, or aerospace applications where failure or malfunction could result in property or environmental damage, serious injury or death. In the aforementioned cases, please contact us before using MGT products.

In principle, we reserve all rights and MGT's general terms and conditions apply. You can find them on our website www.mgt.co.com.